

T Gregorkiewicz

List of Publications by Year in descending order

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papers

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153
docs citations

153
times ranked

2231
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|------|-----------|
| 1 | Space-separated quantum cutting with silicon nanocrystals for photovoltaic applications. Nature Photonics, 2008, 2, 105-109. | 15.6 | 302 |
| 2 | Red spectral shift and enhanced quantum efficiency in phonon-free photoluminescence from silicon nanocrystals. Nature Nanotechnology, 2010, 5, 878-884. | 15.6 | 294 |
| 3 | Step-like enhancement of luminescence quantum yield of silicon nanocrystals. Nature Nanotechnology, 2011, 6, 710-713. | 15.6 | 186 |
| 4 | Silicon quantum dots: surface matters. Journal of Physics Condensed Matter, 2014, 26, 173201. | 0.7 | 163 |
| 5 | Sensitization of Er luminescence by Si nanoclusters. Physical Review B, 2004, 69, . | 1.1 | 131 |
| 6 | Nanosecond Dynamics of the Near-Infrared Photoluminescence of Er-Doped SiO ₂ Sensitized with Si Nanocrystals. Physical Review Letters, 2006, 97, 207401. | 2.9 | 87 |
| 7 | Optically Induced Deexcitation of Rare-Earth Ions in a Semiconductor Matrix. Physical Review Letters, 2002, 89, 227401. | 2.9 | 71 |
| 8 | Energy transfer in Er-doped SiO_2 with Si nanocrystals. Physical Review B, 2008, 78, . | 2.9 | 70 |
| 9 | Direct bandgap optical transitions in Si nanocrystals. JETP Letters, 2010, 90, 758-762. | 0.4 | 59 |
| 10 | Role of Hydrogen in the Formation and Structure of the Si- NL10 Thermal Donor. Physical Review Letters, 1995, 74, 2030-2033. | 2.9 | 57 |
| 11 | Excitation cross section of erbium in semiconductor matrices under optical pumping. Physical Review B, 2001, 64, . | 1.1 | 51 |
| 12 | Microscopic Structure of Er-Related Optically Active Centers in Crystalline Silicon. Physical Review Letters, 2003, 90, 066401. | 2.9 | 50 |
| 13 | EPR studies of heat-treatment centers in p-type silicon. Physical Review B, 1987, 35, 3810-3817. | 1.1 | 49 |
| 14 | Electron paramagnetic resonance versus spin-dependent recombination: Excited triplet states of structural defects in irradiated silicon. Physical Review B, 1995, 52, 1144-1151. | 1.1 | 49 |
| 15 | Infrared absorption in silicon from shallow thermal donors incorporating hydrogen and a link to the NL10 paramagnetic resonance spectrum. Physical Review B, 1996, 54, R6803-R6806. | 1.1 | 49 |
| 16 | Microscopic structure of the NL10 heat-treatment center in silicon: Study by electron-nuclear double resonance. Physical Review B, 1988, 38, 3998-4015. | 1.1 | 47 |
| 17 | Direct Observation of the Two-Stage Excitation Mechanism of Er in Si. Physical Review Letters, 1998, 81, 4748-4751. | 2.9 | 46 |
| 18 | Efficient optical extraction of hot-carrier energy. Nature Communications, 2014, 5, 4665. | 5.8 | 42 |

| # | ARTICLE | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Energy transfer between shallow centers and rare-earth ion cores:Er ³⁺ ion in silicon. Physical Review B, 2000, 61, 5369-5375. | 1.1 | 36 |
| 20 | Isotope Dependence of the Lifetime of the 1136 cm ⁻¹ Vibration of Oxygen in Silicon. Physical Review Letters, 2006, 96, 225503. | 2.9 | 34 |
| 21 | Comparative study of Si-NL8 and Si-NL10 thermal-donor-related EPR centers. Physical Review B, 1990, 41, 12628-12636. | 1.1 | 33 |
| 22 | Optical properties of a single type of optically active center in Si ⁺ •Si:Er nanostructures. Physical Review B, 2004, 70, . | 1.1 | 33 |
| 23 | Optical excitation and external photoluminescence quantum efficiency of Eu ³⁺ in GaN. Scientific Reports, 2014, 4, 5235. | 1.6 | 33 |
| 24 | Electron paramagnetic resonance of molecular hydrogen in silicon. Physical Review Letters, 1993, 71, 117-120. | 2.9 | 32 |
| 25 | EPR spectroscopy of platinum-hydrogen complexes in silicon. Physical Review B, 1994, 49, 13423-13429. | 1.1 | 30 |
| 26 | Donor-State-Enabling Er-Related Luminescence in Silicon: Direct Identification and Resonant Excitation. Physical Review Letters, 2007, 99, 077401. | 2.9 | 29 |
| 27 | Oxygen incorporation in thermal-donor centers in silicon. Physical Review Letters, 1987, 59, 1702-1705. | 2.9 | 28 |
| 28 | Magnetic-resonance studies of interstitial Mn in GaP and GaAs. Physical Review B, 1991, 44, 3012-3019. | 1.1 | 28 |
| 29 | Direct spectral probing of energy storage in Si:Er by a free-electron laser. Applied Physics Letters, 1999, 75, 4121-4123. | 1.5 | 28 |
| 30 | Afterglow effect in photoluminescence of Si:Er. Physical Review B, 2002, 65, . | 1.1 | 28 |
| 31 | Electron-paramagnetic-resonance identification of silver centers in silicon. Physical Review B, 1992, 46, 4544-4550. | 1.1 | 27 |
| 32 | Saturation of luminescence from Si nanocrystals embedded in SiO ₂ . Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 183-187. | 0.8 | 27 |
| 33 | Optically detected microwave-induced impact ionization of ytterbium bound excitons in InP. Applied Physics Letters, 1991, 58, 2237-2239. | 1.5 | 25 |
| 34 | Photoluminescence of erbium-doped silicon: Excitation power and temperature dependence. Journal of Applied Physics, 2000, 88, 1443-1455. | 1.1 | 24 |
| 35 | Si-NL10: Paramagnetic Acceptor State of the Silicon Thermal Donor. Physical Review Letters, 1988, 61, 227-230. | 2.9 | 22 |
| 36 | Self-trapped exciton state in Si nanocrystals revealed by induced absorption. Physical Review B, 2012, 85, . | 1.1 | 22 |

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| 37 | Photoluminescence of silicon thermal donors. Physical Review B, 1993, 47, 7005-7012. | 1.1 | 21 |
| 38 | Lasing in Rare-Earth-Doped Semiconductors: Hopes and Facts. MRS Bulletin, 1999, 24, 27-32. | 1.7 | 21 |
| 39 | Concentration of Er ³⁺ ions contributing to 1.54- μ m emission in Si ^{1-x} Ge ^x :Er nanolayers. Physical Review B, 2007, 76, . | 1.1 | 21 |
| 40 | Electron-paramagnetic-resonance study of heat-treatment centers in n-type silicon. Journal of Applied Physics, 1987, 62, 4404-4405. | 1.1 | 19 |
| 41 | Paramagnetic state of the isolated gold impurity in silicon. Physical Review Letters, 1992, 69, 3185-3188. | 2.9 | 19 |
| 42 | Microscopic model for nonexcitonic mechanism of 1.54- μ m photoluminescence of the Er ³⁺ ion in crystalline Si. Physical Review B, 2003, 67, . | 1.1 | 19 |
| 43 | Increased carrier generation rate in Si nanocrystals in SiO ₂ investigated by induced absorption. Applied Physics Letters, 2011, 99, . | 1.5 | 19 |
| 44 | Observation of Zeeman effect in photoluminescence of Er ³⁺ ion imbedded in crystalline silicon. Physica B: Condensed Matter, 2001, 308-310, 340-343. | 1.3 | 18 |
| 45 | High-Power Eu-Doped GaN Red LED Based on a Multilayer Structure Grown at Lower Temperatures by Organometallic Vapor Phase Epitaxy. MRS Advances, 2017, 2, 159-164. | 0.5 | 18 |
| 46 | Electron-paramagnetic-resonance identification of hydrogen-passivated sulfur centers in silicon. Physical Review B, 1995, 51, 16746-16749. | 1.1 | 17 |
| 47 | Optical gain of the $\langle \text{mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"} \langle \text{mml:mrow} \langle \text{mml:mn} \rangle 1.54 \langle \text{mml:mn} \rangle \langle \text{mml:mtext} \rangle \text{ }\hat{\text{a}}\text{ }\langle \text{mml:mtext} \rangle \langle \text{mml:mi} \rangle \hat{\text{i}} \langle \text{mml:mi} \rangle \langle \text{mml:mtext} \rangle \text{ }\mu \langle \text{mml:mtext} \rangle \text{ }\hat{\text{a}} \langle \text{mml:mtext} \rangle \text{ }\text{in MBE-grown Si:Er nanolayers. Physical Review B, 2010, 81, .$ | 1.1 | 17 |
| 48 | Carrier dynamics in Si nanocrystals in an SiO ₂ matrix investigated by transient light absorption. Physical Review B, 2013, 88, . | 1.1 | 17 |
| 49 | Metastable thermal donor states in germanium: Identification by electron paramagnetic resonance. Physical Review B, 1990, 42, 9802-9809. | 1.1 | 16 |
| 50 | Shallow thermal donors associated with H, Al and N in annealed Czochralski silicon distinguished by infrared spectroscopy. Semiconductor Science and Technology, 1997, 12, 1404-1408. | 1.0 | 15 |
| 51 | Copper-related defects in silicon: Electron-paramagnetic-resonance identification. Physical Review B, 1997, 56, 4620-4625. | 1.1 | 15 |
| 52 | Optical properties of a silver-related defect in silicon. Physical Review B, 2003, 67, . | 1.1 | 15 |
| 53 | Auger deexcitation of Er ³⁺ ions in crystalline Si optically induced by midinfrared illumination. Physical Review B, 2003, 68, . | 1.1 | 15 |
| 54 | Theoretical modeling of thermally activated luminescence quenching processes in Si:Er. Physical Review B, 2005, 72, . | 1.1 | 15 |

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|----|---|-----|-----------|
| 55 | On optical activity of Er ³⁺ ions in Si-rich SiO ₂ waveguides. Applied Physics Letters, 2006, 89, 171908. | 1.5 | 15 |
| 56 | Photon cutting for excitation of Er ³⁺ ions in SiO ₂ sensitized by Si quantum dots. Physical Review B, 2011, 84, . | 1.1 | 15 |
| 57 | Spin delocalization of interstitial iron in silicon. Physical Review B, 1986, 34, 4511-4520. | 1.1 | 13 |
| 58 | Magnetic resonance spectroscopy of zinc doped silicon. Solid State Communications, 1990, 75, 115-120. | 0.9 | 13 |
| 59 | Magnetic resonance spectroscopy in silver-doped silicon. Journal of Applied Physics, 1993, 73, 1797-1801. | 1.1 | 13 |
| 60 | Silicon electron-nuclear double-resonance study of the NL10 heat-treatment center. Physical Review B, 1989, 39, 1648-1658. | 1.1 | 12 |
| 61 | Electron paramagnetic resonance study of the NL51 spectrum in hydrogen-implanted silicon. Solid State Communications, 1994, 90, 401-404. | 0.9 | 12 |
| 62 | Endor Identification of a Hydrogen-Passivated Thermal Donor. Materials Science Forum, 1995, 196-201, 849-854. | 0.3 | 12 |
| 63 | Excitation paths in RE-doped III-V semiconductors. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 105, 141-145. | 1.7 | 12 |
| 64 | Photoluminescence studies on thermal donors in boron- and aluminum-doped silicon. Physical Review B, 1992, 46, 2034-2040. | 1.1 | 11 |
| 65 | Er ³⁺ photoluminescence excitation spectra in erbium-doped epitaxial silicon structures. Physics of the Solid State, 2004, 46, 97-100. | 0.2 | 11 |
| 66 | Strong infrared photoluminescence in highly porous layers of large faceted Si crystalline nanoparticles. Scientific Reports, 2016, 6, 25664. | 1.6 | 11 |
| 67 | Hot-carrier-mediated impact excitation of Er ³⁺ ions in SiO ₂ sensitized by Si Nanocrystals. Applied Physics Letters, 2018, 113, 031109. | 1.5 | 11 |
| 68 | Excitation and DE-Excitation of Yb ³⁺ in InP and Er ³⁺ in Si: Photoluminescence and Impact Ionization Studies. Materials Research Society Symposia Proceedings, 1996, 422, 207. | 0.1 | 10 |
| 69 | Microscopic evidence for role of oxygen in luminescence of Er ³⁺ ions in Si: Two-color and pump-probe spectroscopy. Physical Review B, 2008, 78, . | 1.1 | 10 |
| 70 | Optically detected Auger recombinations in erbium- and ytterbium-doped InP. Applied Physics Letters, 1991, 59, 3279-3281. | 1.5 | 9 |
| 71 | Photoluminescence measurements on erbium-doped silicon. Semiconductor Science and Technology, 1995, 10, 666-671. | 1.0 | 9 |
| 72 | Role of Shallow Bound States in Emission Processes of Rare-Earth Doped Semiconductors. Physica Status Solidi (B): Basic Research, 1998, 210, 737-745. | 0.7 | 9 |

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| 73 | Photoluminescence excitation spectroscopy of erbium in epitaxially grown Si:Er structures. Optical Materials, 2005, 27, 890-893. | 1.7 | 9 |
| 74 | Dynamics and microscopic origin of fast $1.5\mu\text{m}$ emission in Er-doped SiO ₂ sensitized thermal donors and oxygen-related complexes in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 291-297. | 1.1 | 9 |
| 75 | Thermal donors and oxygen-related complexes in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1989, 4, 291-297. | 1.7 | 8 |
| 76 | Sensitive electron paramagnetic resonance spectrometer for studying defects in semiconductors. Review of Scientific Instruments, 1992, 63, 5742-5749. | 0.6 | 8 |
| 77 | Role of electron traps in the excitation and de-excitation mechanism of Yb ³⁺ in InP. Journal of Applied Physics, 1995, 77, 1523-1530. | 1.1 | 8 |
| 78 | Electron-paramagnetic-resonance study of silver-induced defects in silicon. Physical Review B, 1997, 56, 4614-4619. | 1.1 | 8 |
| 79 | Free-electron laser studies of energy transfer mechanisms in semiconductors doped with transition series ions. Journal of Luminescence, 2001, 94-95, 243-248. | 1.5 | 8 |
| 80 | 780-meV photoluminescence band in silver-doped silicon: Isotope effect and time-resolved spectroscopy. Physical Review B, 2001, 65, . | 1.1 | 8 |
| 81 | Two-color mid-infrared spectroscopy of optically doped semiconductors. Journal of Luminescence, 2003, 102-103, 85-90. | 1.5 | 8 |
| 82 | Time-resolved free-electron laser spectroscopy of a copper isoelectronic center in silicon. Physical Review B, 2005, 71, . | 1.1 | 8 |
| 83 | Optical spectroscopy of carrier relaxation processes in Si nanocrystals. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 190-193. | 1.7 | 8 |
| 84 | Aluminum incorporation in the Si-NL10 thermal donor. Physical Review B, 1992, 46, 4582-4589. | 1.1 | 7 |
| 85 | A New Bistable Shallow Thermal Donor in Al-Doped Si. Materials Science Forum, 1993, 143-147, 1185-1190. | 0.3 | 7 |
| 86 | Hydrogen passivation of the selenium double donor in silicon: A study by magnetic resonance. Physical Review B, 2000, 61, 7448-7458. | 1.1 | 7 |
| 87 | The Auger process of luminescence quenching in Si/Si:Er multilayers. Journal of Physics Condensed Matter, 2005, 17, S2191-S2195. | 0.7 | 7 |
| 88 | Terahertz modulation of the blue photoluminescence in ZnSe. Physical Review B, 2005, 72, . | 1.1 | 7 |
| 89 | Non-radiative sub-microsecond recombination of excited Er ³⁺ ions in SiO ₂ sensitized with Si nanocrystals. Physica E: Low-Dimensional Systems and Nanostructures, 2007, 38, 144-147. | 1.3 | 7 |
| 90 | Stallinga, Gregorkiewicz, and Ammerlaan Reply. Physical Review Letters, 1994, 73, 1457-1457. | 2.9 | 6 |

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| 91 | High-Field EPR Spectroscopy of Thermal Donors in Silicon. Materials Science Forum, 1997, 258-263, 373-378. | 0.3 | 6 |
| 92 | Terahertz-assisted excitation of the 1.5 μm photoluminescence of Er in crystalline Si. Physical Review B, 2004, 70, . | 1.1 | 6 |
| 93 | On 2.7 μm Emission from Er-doped Large Bandgap Hosts. Materials Research Society Symposia Proceedings, 2005, 866, 7. | 0.1 | 6 |
| 94 | Thermally Activated Emission from Direct Bandgap-Like Silicon Quantum Dots. ECS Journal of Solid State Science and Technology, 2013, 2, R97-R99. | 0.9 | 6 |
| 95 | Generation of hot carriers for photon management in future photovoltaics. Solar Energy Materials and Solar Cells, 2015, 135, 67-71. | 3.0 | 6 |
| 96 | Photoluminescence on oxygen-rich acceptor-doped silicon. Journal of Physics C: Solid State Physics, 1987, 20, 2183-2191. | 1.5 | 5 |
| 97 | Photoluminescence and excitation spectroscopy of the 1.5 μm Er-related band in MBE-grown GaN layers. Superlattices and Microstructures, 2004, 36, 701-705. | 1.4 | 5 |
| 98 | Trapping time of excitons in Si nanocrystals embedded in a $\langle \text{SiO}_2 \rangle$ matrix. Physical Review B, 2017, 95, . | 1.1 | 5 |
| 99 | Transition metal impurities in silicon. , 1988, , 244-261. | | 4 |
| 100 | Nuclear interactions of defects in semiconductors $\hat{\epsilon}$ magnetic resonance measurements. Nuclear Instruments & Methods in Physics Research B, 1992, 63, 154-162. | 0.6 | 4 |
| 101 | Excitation and De-Excitation Mechanisms of Rare-Earth Ions in III-V Compounds: Optically Detected Microwave-Induced Impact Ionization of Yb Dopant in Inp. Materials Research Society Symposia Proceedings, 1993, 301, 239. | 0.1 | 4 |
| 102 | Hydrogen Passivation of the Sulfur Double Donor in Silicon Investigated by EPR and ENDOR. Materials Science Forum, 1995, 196-201, 855-860. | 0.3 | 4 |
| 103 | Magnetic resonance spectroscopy of hydrogen-passivated double donors in silicon. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1996, 36, 138-141. | 1.7 | 4 |
| 104 | Influence of p-n junction formation at a Si/Si:Er interface on low-temperature excitation of Er ³⁺ ions in crystalline silicon. Physical Review B, 2001, 64, . | 1.1 | 4 |
| 105 | Silicon-based all-optical memory elements for 1.54 μm photonics. Solid-State Electronics, 2003, 47, 165-168. | 0.8 | 4 |
| 106 | Magneto-optical study of Er ³⁺ -related center in selectively doped Si:Er. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 544-546. | 1.3 | 4 |
| 107 | 1.54 μm Si:Er light emitting diode with memory function. Applied Physics Letters, 2006, 88, 201101. | 1.5 | 4 |
| 108 | Space-separated quantum cutting in differently prepared solid-state dispersions of Si nanocrystals and Er ³⁺ ions in SiO ₂ . Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 159-160, 87-89. | 1.7 | 4 |

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| 109 | Magnetic Resonance Investigations of Thermal Donors in Silicon. , 1996, , 61-82. | | 4 |
| 110 | High-resolution EPR spectroscopy of the Si-NL10 thermal donor. Physical Review B, 1992, 45, 5873-5878. | 1.1 | 3 |
| 111 | Optically induced Auger recombination of Yb ³⁺ in p-type InP. Physica B: Condensed Matter, 2001, 308-310, 884-887. | 1.3 | 3 |
| 112 | Photoluminescence from Si:Er under front and backside excitation. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2001, 81, 59-61. | 1.7 | 3 |
| 113 | Erbium Photoluminescence Excitation Spectroscopy in Si : Er Epitaxial Structures. Physics of the Solid State, 2005, 47, 86. | 0.2 | 3 |
| 114 | Investigation of saturation and excitation behavior of 1.5 μ m emission from Er ³⁺ ions in SiO ₂ sensitized with Si nanocrystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 2312-2317. | 0.8 | 3 |
| 115 | Characterization of Defect Centres in Semiconductors by Advanced ENDOR Techniques. Acta Physica Polonica A, 1991, 80, 161-170. | 0.2 | 3 |
| 116 | Thermal Donor Generation in Boron- and Aluminium-Doped Czochralski Silicon. Acta Physica Polonica A, 1991, 80, 345-348. | 0.2 | 3 |
| 117 | Oxygen related mechanism of reverse annealing for boron implants in silicon. Radiation Effects, 1984, 85, 249-254. | 0.4 | 2 |
| 118 | Silicon Thermal Donors: Photoluminescence and Magnetic Resonance Study of Boron- and Aluminum-Doped Silicon. Materials Science Forum, 1992, 83-87, 407-412. | 0.3 | 2 |
| 119 | Photoluminescence Study of the 779-meV Band in Silver-Doped Silicon. Materials Science Forum, 1994, 143-147, 755-760. | 0.3 | 2 |
| 120 | The 4f Intrashell Transitions of Ytterbium in Indium Phosphide. Materials Research Society Symposia Proceedings, 1996, 422, 161. | 0.1 | 2 |
| 121 | Photoluminescence Study of Erbium in Silicon with a Free-Electron Laser. Materials Science Forum, 1997, 258-263, 1497-1502. | 0.3 | 2 |
| 122 | Excitation mechanism of Er in Si studied with a free-electron laser. Journal of Luminescence, 1998, 80, 291-295. | 1.5 | 2 |
| 123 | Atomic and electronic structure of hydrogen-passivated double selenium donors in silicon. Physica B: Condensed Matter, 1999, 273-274, 239-242. | 1.3 | 2 |
| 124 | The photoluminescence mechanism of erbium in silicon: intensity dependence on excitation power and temperature. Physica B: Condensed Matter, 1999, 273-274, 338-341. | 1.3 | 2 |
| 125 | Si Nanocrystals as Sensitizers for Er PL in SiO ₂ . Materials Research Society Symposia Proceedings, 2003, 770, 691. | 0.1 | 2 |
| 126 | Terahertz electromagnetic transitions observed within the 4 ^{15/2} ground multiplet of Er ³⁺ ions in Si. Physical Review B, 2009, 79, . | 1.1 | 2 |

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| 127 | Evaluation of free carrier losses to 1.54 μ m emission in Si/Si:Er nanolayers on SOI substrate for optical gain observation. <i>Optical Materials</i> , 2011, 33, 1094-1096. | 1.7 | 2 |
| 128 | Infrared Absorption Study of Thermally Generated Shallow Donor Centers in Czochralski Silicon. <i>Acta Physica Polonica A</i> , 1992, 82, 677-680. | 0.2 | 2 |
| 129 | EPR studies of the annealing of damage produced by boron implantation of silicon single crystals. <i>Radiation Effects</i> , 1982, 68, 69-76. | 0.4 | 1 |
| 130 | Electron paramagnetic resonance of silicon implanted with boron and arsenic ions. <i>Radiation Effects</i> , 1983, 77, 195-203. | 0.4 | 1 |
| 131 | High-field EPR spectroscopy of thermal donors in silicon. <i>Physica B: Condensed Matter</i> , 1992, 177, 476-480. | 1.3 | 1 |
| 132 | Spectroscopic probing of defect-related energy storage in silicon doped with erbium. <i>Physica B: Condensed Matter</i> , 1999, 273-274, 326-329. | 1.3 | 1 |
| 133 | Photoluminescence quenching in InP:Yb with a free-electron laser. <i>Applied Surface Science</i> , 2003, 208-209, 23-26. | 3.1 | 1 |
| 134 | Erbium Excitation in a SiO ₂ : Si-nc Matrix under Pulsed Pumping. <i>Physics of the Solid State</i> , 2005, 47, 110. | 0.2 | 1 |
| 135 | Excitation efficiency and saturation dynamics of near-infrared emission from Si nanocrystals embedded in a SiO ₂ -matrix. <i>Journal of Physics: Conference Series</i> , 2009, 165, 012018. | 0.3 | 1 |
| 136 | Step-like increase of quantum yield of 1.5 μ m Er-related emission in SiO ₂ doped with Si nanocrystals. <i>Journal of Applied Physics</i> , 2015, 117, 064303. | 1.1 | 1 |
| 137 | Trapping of Molecular Hydrogen in Porous Silicon and at Si/SiO ₂ Interfaces and a Possible Reinterpretation of the Pb Center. <i>Materials Research Society Symposia Proceedings</i> , 1993, 324, 385. | 0.1 | 0 |
| 138 | Tracking recombination processes in Si : Er with a free-electron laser. <i>Journal of Luminescence</i> , 2000, 87-89, 96-100. | 1.5 | 0 |
| 139 | Time-resolved investigation of the mid-infrared-induced enhancement of Er ³⁺ emission in Si. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 337-339. | 1.3 | 0 |
| 140 | Erbium excitation across the bulk of silicon wafer: an effect of p-n junction at Si/Si:Er interface. <i>Physica B: Condensed Matter</i> , 2001, 308-310, 357-360. | 1.3 | 0 |
| 141 | Mid-infrared induced quenching of photoluminescence in Si:Er. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001, 81, 80-82. | 1.7 | 0 |
| 142 | Semiconductors: Rare Earth Impurities. , 2001, , 8392-8396. | | 0 |
| 143 | Spectroscopic characterization of Er-1 center in selectively doped silicon. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003, 105, 150-152. | 1.7 | 0 |
| 144 | Pump-probe investigations of THz transitions in Si/Si:Er ³⁺ nanolayers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 146, 160-162. | 1.7 | 0 |

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| 145 | Mid-infrared spectroscopy of the Er-related donor state in Si/Si:Er ³⁺ nanolayers. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2008, 146, 131-134. | 1.7 | 0 |
| 146 | Optical properties of Si/Si:Er multi-nanolayer structures grown by SMBE method. <i>Physica B: Condensed Matter</i> , 2009, 404, 5132-5135. | 1.3 | 0 |
| 147 | On relation between the 1.5 μ m Er-related emission and 9 μ m vibrational modes of oxygen in silicon. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2009, 41, 1052-1054. | 1.3 | 0 |
| 148 | Fast dynamics of 1.5 μ m photoluminescence in Er-doped SiO ₂ sensitized with Si nanocrystals. <i>Optical Materials</i> , 2011, 33, 1091-1093. | 1.7 | 0 |
| 149 | Manipulating Photon Energy with Si Nanocrystals. , 2012, , . | | 0 |
| 150 | Si nanocrystals for photon management. , 2012, , . | | 0 |
| 151 | Enhancement of luminescence quantum yield of 1.5 μ m emission from Er-doped SiO ₂ sensitized with Si nanocrystals. <i>Materials Research Society Symposia Proceedings</i> , 2014, 1592, 1. | 0.1 | 0 |
| 152 | Magnetic resonance spectroscopy of hydrogen-passivated double donors in silicon. , 1996, , 138-141. | | 0 |